

8N90

Power MOSFET

8A, 900V N-CHANNEL POWER MOSFET

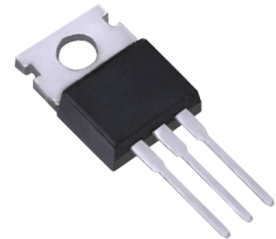
■ DESCRIPTION

The UTC **8N90** is an N-channel mode power MOSFET, using UTC's advanced technology to provide customers planar stripe and DMOS technology. This technology allows a minimum on-state resistance, superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

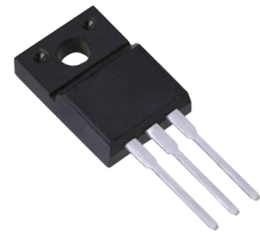
The UTC **8N90** is generally applied in high efficiency switch mode power supplies.

■ FEATURES

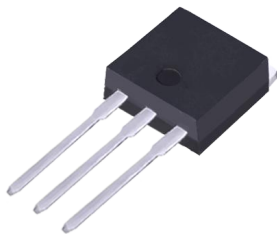
- * $R_{DS(ON)} < 1.55\Omega @ V_{GS} = 10V$
- * Fast Switching Speed
- * 100% Avalanche Tested
- * Improved dv/dt Capability



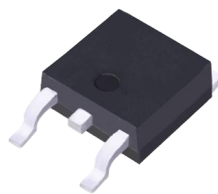
TO-220



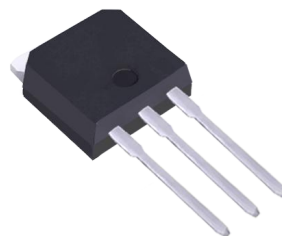
TO-220F



TO-262



TO-263



TO-251



TO-252

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		V_{DSS}	900	V
Gate to Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current ($T_C=25^\circ\text{C}$)		I_D	8	A
Pulsed Drain Current (Note 2)		I_{DM}	25	A
Avalanche Current (Note 2)		I_{AR}	6.3	A
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	850	mJ
Repetitive Avalanche Energy (Note 2)		E_{AR}	17.1	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.0	V/ns
Power Dissipation ($T_C=25^\circ\text{C}$)	TO-220	P_D	147	W
	TO-220F2		62	
Linear Derating Factor above $T_C=25^\circ\text{C}$	TO-220		1.17	W/ $^\circ\text{C}$
	TO-220F2		0.5	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L=27\text{mH}$, $I_{AS}=8\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$

4. $I_{SD}\leq 8\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.85	$^\circ\text{C}/\text{W}$
	TO-220F2		2.0	

■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	900			V
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.95		V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =900V, V _{GS} =0V			10	μA
		V _{DS} =720V, T _C =125°C			100	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	3.0		5.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =4A		1.16	1.55	Ω
Forward Transconductance (Note 2)	g _{FS}	V _{DS} =50V, I _D =4A		5.5		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		1600	2080	pF
Output Capacitance	C _{OSS}			130	170	pF
Reverse Transfer Capacitance	C _{RSS}			12	15	pF
SWITCHING PARAMETERS (Note 2, Note 3)						
Total Gate Charge	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A		54		nC
Gate-Source Charge	Q _{GS}			12		nC
Gate-Drain Charge	Q _{GD}			16		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =30V, I _D =0.5A, R _G =25Ω		95		ns
Turn-ON Rise Time	t _R			220		ns
Turn-OFF Delay Time	t _{D(OFF)}			275		ns
Turn-OFF Fall Time	t _F			175		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				8	A
Maximum Body-Diode Pulsed Current	I _{SM}				32	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =8A, V _{GS} =0V			1.4	V

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
 2. Essentially independent of operating temperature

■ TYPICAL CHARACTERISTICS

